

## I) IC Lab Schedule (2008 Fall PRISM)

DATE	LAB	DESCRIPTION
September 16		No Lab
September 23	1	Lab tour; Safety discussion; Determining charge carrier type; Determining resistivity.
September 30	2	Wafer clean; Wet oxidation.
October 07	3	Photolithography Level 1; Oxide etch; Strip resist; Wafer clean; Spin on dopant glass.
October 14	4	Diffuse; Etch dopant glass; Demonstrate diode electrical characteristics.
October 21		No Lab
October 28		Fall Break
November 04	5	Photolithography Level 2; Oxide etch; Strip resist; Wafer clean; Gate oxidation
November 11	6	Photolithography Level 3; Oxide etch; Strip resist; Photolithography Level 4.
November 18	7	Evaporate aluminum; Lift-off; Sinter & Anneal; Solder to glass slide
November 25	8	Measurement Experiments 1-6.
December 02	9	Measurement Experiments 1-6.
December 09	10	Measurement Experiments 1-6.
January 06	11	Measurement Experiments 1-6.